

#### Features:

- 1200V Schottky Diode
- Zero Reverse Recovery Current
- High Frequency Operation
- Positive Temperature Coefficient
- Temperature independent Switching

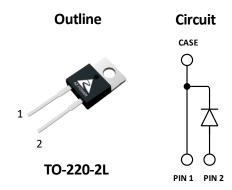
#### **Benefits:**

- Unipolar Rectifier
- Minimal switching loss
- Higher Efficiency
- Low cooling requirement

| Symbol                    | Value | Unit |
|---------------------------|-------|------|
| $V_{RRM}$                 | 1200  | V    |
| I <sub>F</sub> (Tc=158ºC) | 12    | А    |
| Qc                        | 110   | nC   |

# **Applications:**

- Switch Mode Power Supply
- Booster diodes in PFC, DC/DC
- AC/DC converters



## **Maximum Ratings**

| Symbol           | Parameter                                  | Value            | Unit | Test Conditions   |
|------------------|--|------------------|------|---|
| $V_R$            | DC Peak Reverse Voltage                    | 1200             | V    | T <sub>J</sub> =25°C  |
| V <sub>RRM</sub> | Repetitive Peak Reverse Voltage            | 1200             | V    | T <sub>J</sub> =25°C  |
| V <sub>RSM</sub> | Surge Peak Reverse Voltage                 | 1300             | V    | T <sub>J</sub> =25°C  |
| I <sub>F</sub>   | Continuous Forward Current                 | 49.6<br>26<br>12 | А    | T <sub>C</sub> =25°C<br>T <sub>C</sub> =125°C<br>T <sub>C</sub> =158°C                                    |
| I <sub>FRM</sub> | Repetitive Peak Forward Surge<br>Current   | 122<br>98        | А    | $T_{\text{C}}$ =25°C, $T_{\text{P}}$ =10ms, Half Sine Wave Tc=125°C, $T_{\text{P}}$ =10ms, Half Sine Wave |
| I <sub>FSM</sub> | Non-Repetitive Peak Forward  Surge Current | 145<br>128       | А    | $T_C$ =25°C, $T_P$ =10ms, Half Sine Wave<br>Tc=125°C, $T_P$ =10ms, Half Sine Wave                         |
| P <sub>D</sub>   | Power Dissipation                          | 192<br>64        | W    | T <sub>C</sub> =25°C<br>Tc=125°C  |
| $T_{J,max}$      | Operating Junction Temperature             | 175              | °C   |   |
| T <sub>stg</sub> | Storage Temperature Range                  | -55 to 175       | °C   |   |



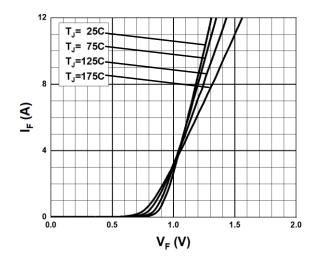
## **Thermal characteristics**

| Symbol            | Parameter          | Min. | Тур. | Max. | Unit |
|-------------------|--------------------|------|------|------|------|
| R <sub>thJC</sub> | Thermal resistance |      | 0.78 |      | °C/W |

## **Electrical Characteristics**

| Symbol Pa                              | Davanastav              | Value   |      | 11   | To de Constitutions                        |   |
|--|-------------------------|---------|------|------|--|---|
|  | Parameter               | Min.    | Тур. | Max. | Unit                                       | Test Conditions                                     |
| $V_{DC}$                               | DC Blocking Voltage     | 1200    |      |      | V  | I <sub>R</sub> =100μA, Τ <sub>J</sub> =25°C         |
| V                                      | Forward Voltage         |         | 1.35 | 1.6  | V  | I <sub>F</sub> =12A, T <sub>J</sub> =25°C           |
| V <sub>F</sub>                         | Forward Voltage         |         | 1.6  | 1.9  |  | I <sub>F</sub> =12A, T <sub>J</sub> =175°C          |
|  | Reverse Current         |         | 5    | 100  | μΑ   | V <sub>R</sub> =1200V, T <sub>J</sub> =25°C         |
| I <sub>R</sub> Reverse Curre           | Reverse Current         |         | 10   | 200  |  | V <sub>R</sub> =1200V, T <sub>J</sub> =175°C        |
| Q <sub>C</sub> Total Capacitive Charge | Tatal Canacitive Chaves | Charres | 110  |      |  | I <sub>F</sub> =12A, dI/dt=400A/μs                  |
|  | ] ]                     | 110     |      | nC   | T <sub>J</sub> =25°C, V <sub>R</sub> =800V |   |
| С                                      | Total Capacitance       |         | 715  |      | pF   | V <sub>R</sub> =1V, T <sub>J</sub> =25°C, f=1 MHz   |
|  |                         |         | 98   |      |  | V <sub>R</sub> =400V, T <sub>J</sub> =25°C, f=1 MHz |
|  |                         |         | 82   |      |  | V <sub>R</sub> =800V, T <sub>J</sub> =25°C, f=1 MHz |

## **Typical Performance**



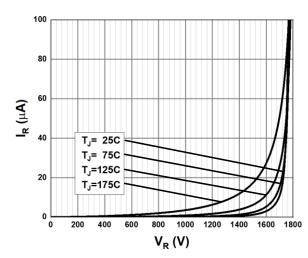
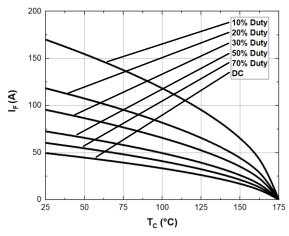




Fig. 1 Forward Characteristics

#### Fig. 2 Reverse Characteristics

# **Typical Performance**





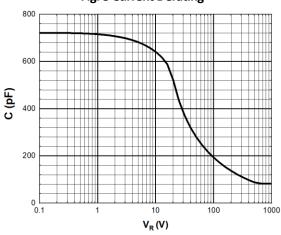


Fig. 5 Capacitance vs. Reverse Voltage

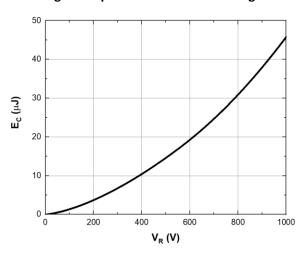


Fig. 7 Capacitance stored Energy

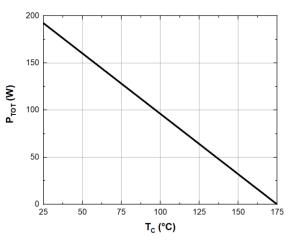


Fig. 4 Power Derating

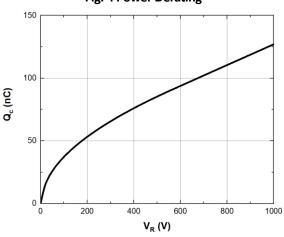


Fig. 6 Recovery Charge vs. Reverse Voltage

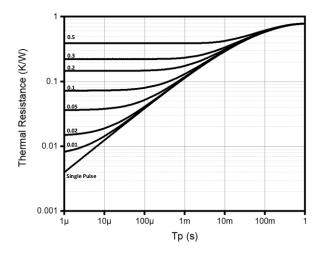
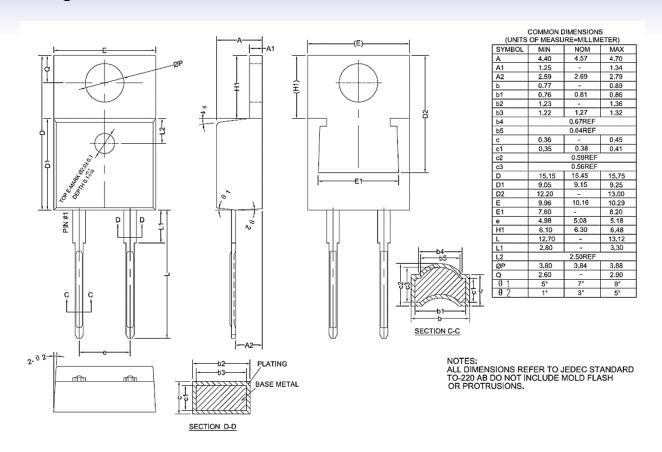


Fig. 8 Transient Thermal Resistance



Package TO-220-2L (Unit: mm)



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